NSN 5962-01-111-7481

Memory Microcircuit - Page 1 of 1

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Maximum Power Dissipation Rating:

500.0 milliwatts

Operating Tempurature Range:

-0.0/+75.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Monolithic and programmable and 3-state output

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

10 input

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

70.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Rom

Test Data Document:

05869-726009-1 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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